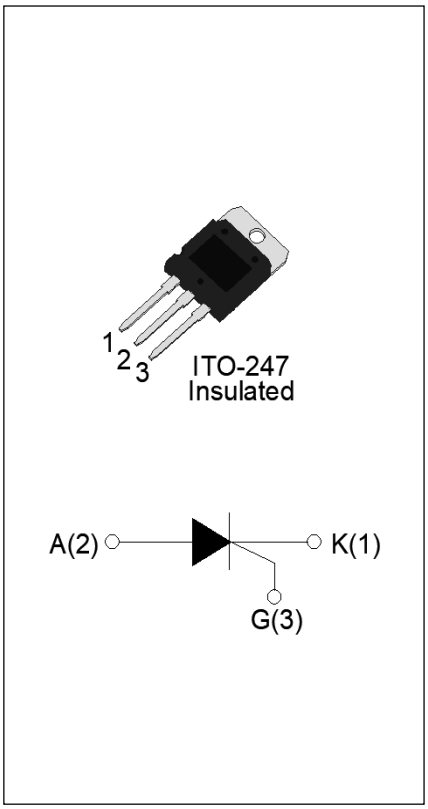
JCT16110IS 110A SCR

Rev.A.1.0

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT16110IS SCR provides high dv/dt rate with strong resistance to electromagnetic interference. It is especially recommended for use on solid state relay, UPS, SVC, power charger, T-tools etc. From all three terminals to external heatsink,JCT16110IS provides a rated insulationvoltage of 2500 $V_{RMS,}$ Package ITO-247 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	110	A
V_{DRM} /V_{RRM}	1600	V
I_{GT}	10-80	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	℃
Operating junction temperature range	T_j	-40-125	℃
Repetitive peak off-state voltage (T_j=25℃)	V_{DRM}	1600	V
Repetitive peak reverse voltage (T_j=25℃)	V_{RRM}	1600	V
Average on-state current (T_C≤73℃)	$I_{T(AV)}$	70	A
RMS on-state current (T_C≤73℃)	$I_{T(RMS)}$	110	A
Non repetitive surge peak on-state current (t_p=10ms , T_j=25℃)	I_{TSM}	1100	A
Non repetitive surge peak on-state current (t_p=8.3ms , T_j=25℃)		1200	
I^2t value for fusing (t_p=10ms , T_j=25℃)	I^2t	6050	A^2s
Critical rate of rise of on-state current (I_G=2×I_{GT} , f=100Hz , T_j=125℃)	dI/dt	200	A/μs

Peak gate current (t_p=20μs , T_j=125℃)	I_{GM}	12	A
Average gate power dissipation (T_j=125℃)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage (T_j=25℃; non-repetitive,off-state;FIG.7)	V_{pp}	1.3	kV

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	10	-	80	mA
V_{GT}		-	-	1.3	V
V_{GD}	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ	0.25	-	-	V
I_L	I_G=1.2I_{GT}	-	-	250	mA
I_H	I_T=1A	-	-	200	mA
dV/dt	V_D=1070V Gate Open T_j=125℃	2000	-	-	V/μs
t_{on}	I_G=100mA I_A=1A I_R=100mA T_j=25℃	-	8	-	μs
t_{off}		-	200	-	

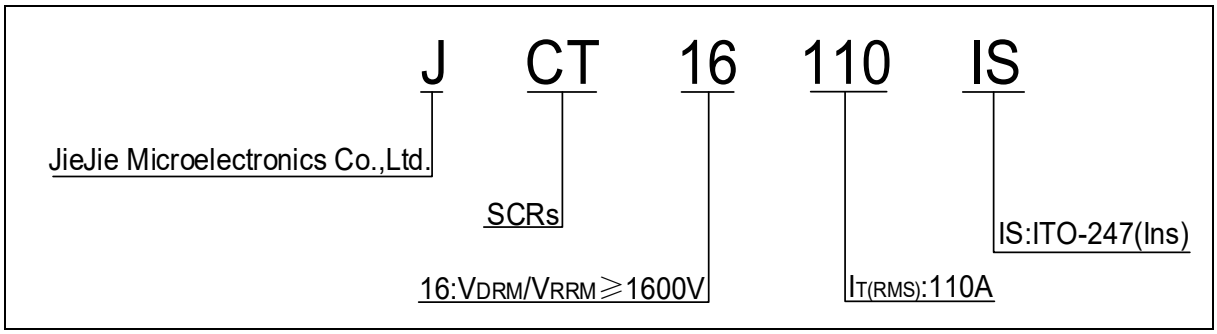
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM}=150A t_p=380μs	T_j=25℃	1.6	V
V_{TO}	Threshold voltage	T_j=125℃	0.76	V
R_D	Dynamic resistance	T_j=125℃	5.6	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	15	μA
I_{RRM}		T_j=125℃	10	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	0.35	℃/W
$R_{th(j-a)}$	junction to ambient (DC)	50	℃/W

ORDERING INFORMATION



MARKING

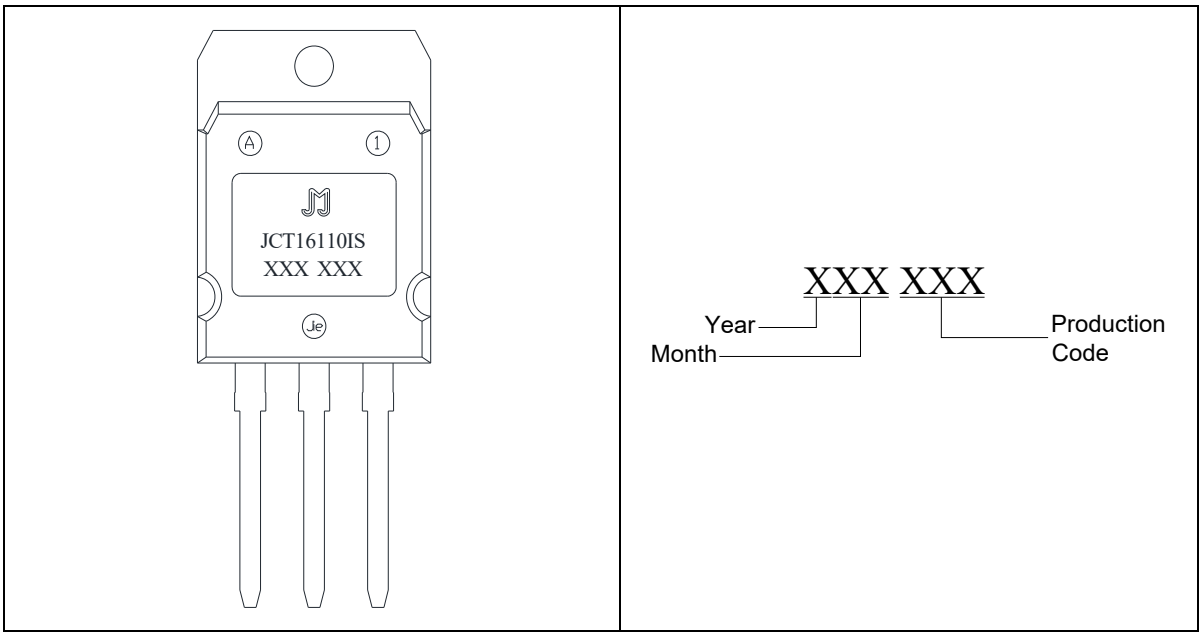


FIG.1 Maximum power dissipation versus RMS on-state current

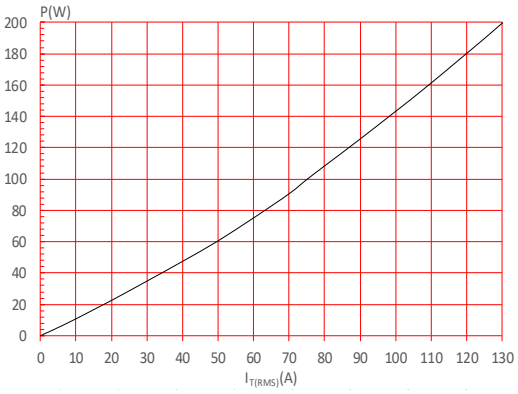


FIG.2: RMS on-state current versus case temperature

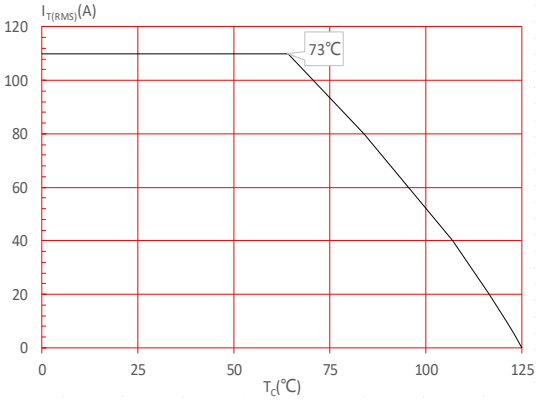


FIG.3: Surge peak on-state current versus number of cycles

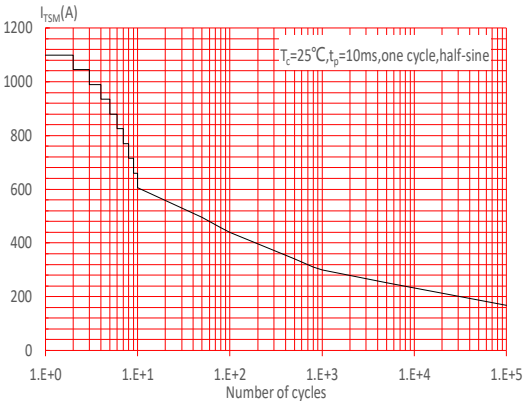


FIG.4: On-state characteristics

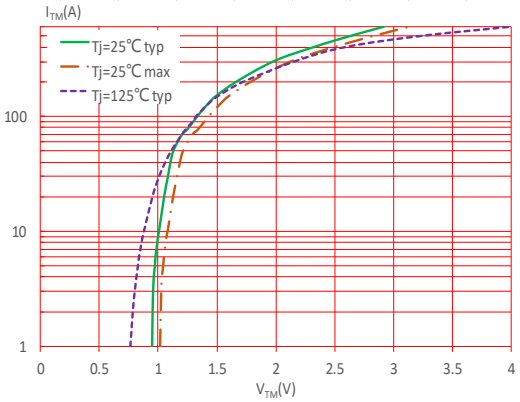


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<10ms, and corresponding value of I^2t (dI/dt<200A/μs)

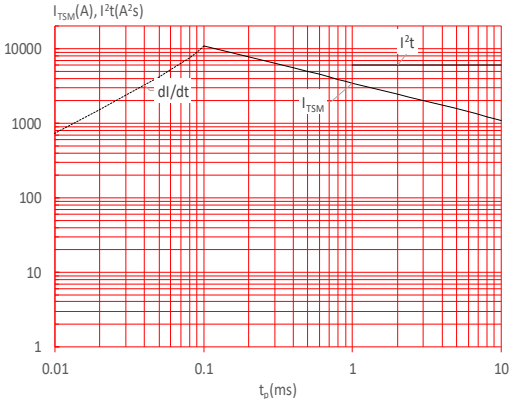


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

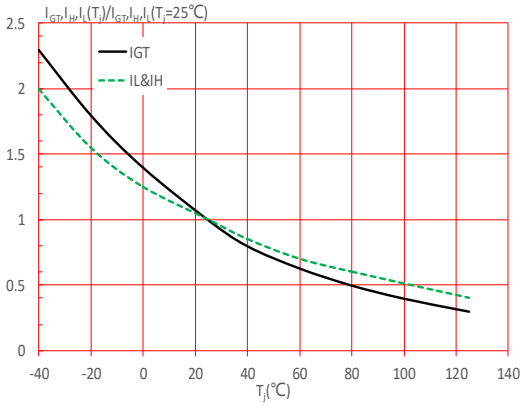
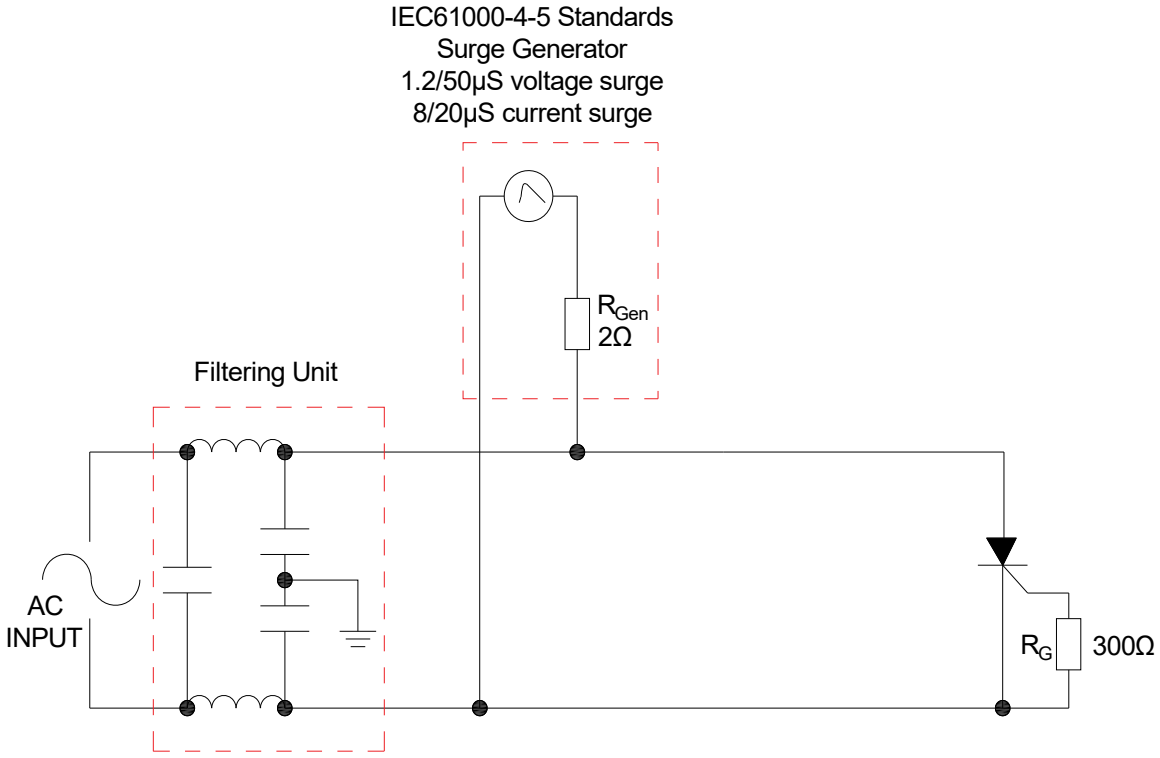


FIG.7：Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



SHAPING AND SOLDERING PARAMETERS

Refer to《Instructions for installation of plastic-sealed in-line power devices》released by JieJie

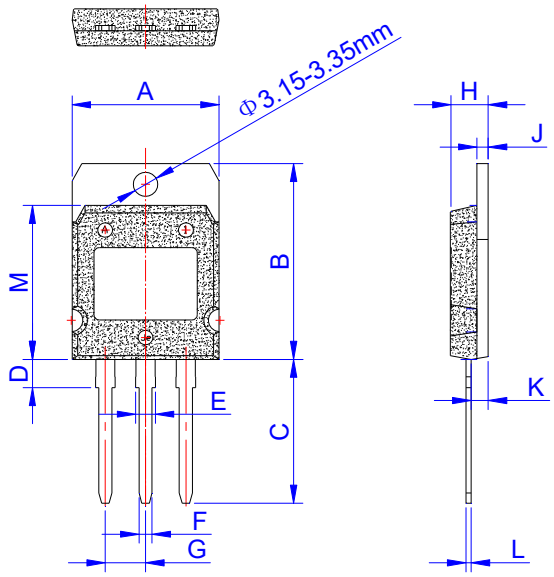
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT16110IS	1600	10-80	ITO-247(Ins)	25	Tube

Document Revision History

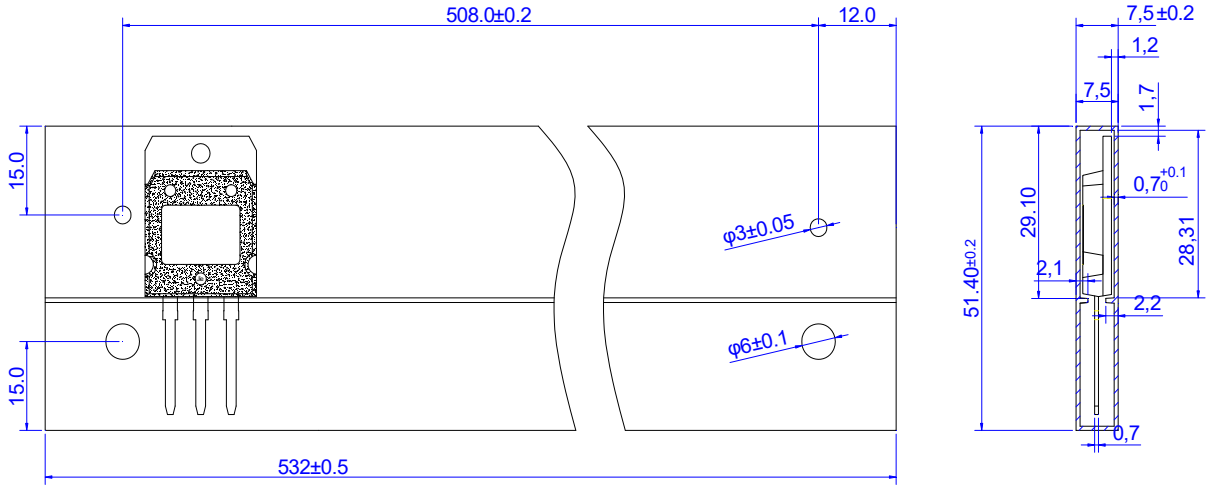
Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	19.7	19.9	20.1	0.776	0.783	0.791
B	26.9	27.1	27.3	1.059	1.067	1.075
C	19.4	19.9	20.4	0.764	0.783	0.803
D	3.80	3.90	4.00	0.150	0.154	0.157
E	2.56	2.66	2.76	0.101	0.105	0.109
F	1.66	1.76	1.86	0.065	0.069	0.073
G	5.25		5.65	0.207		0.222
H	5.05	5.10	5.50	0.199	0.201	0.217
J	1.45	1.50	1.55	0.057	0.059	0.061
K	2.20	2.30	2.40	0.087	0.091	0.094
L	0.60	0.70	0.80	0.024	0.028	0.031
M	21.2	21.3	21.4	0.835	0.839	0.843

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
ITO-247	TUBE	25	400	1,600

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